/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

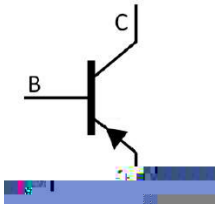
MJD41C

Complement to MJD41C.

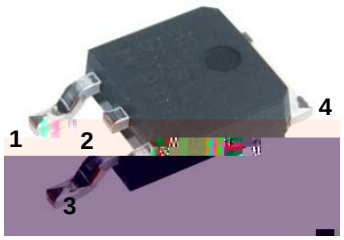
/ Applications

Medium power linear switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

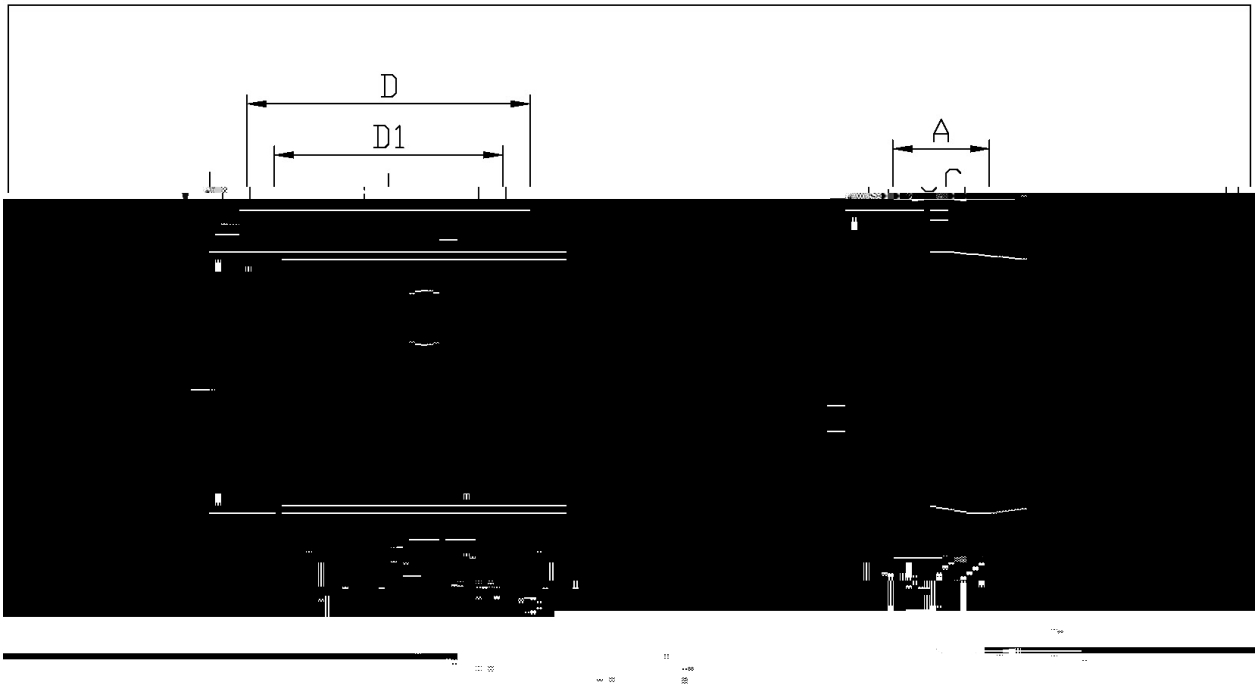
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Base Current - Continuous	I_B	-2.0	A
Collector Power Dissipation	P_D	1.75	W
Collector Power Dissipation	$P_D(T_C=25$)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-30mA I_B=0	-100			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=-60V I_B=0			-50	μA
Collector Cut-Off Current	I_{CES}	V_{CE}=-100V V_{BE}=0			-10	μA
Emitter Cut-Off Current	I					

/ Electrical Characteristic Curve

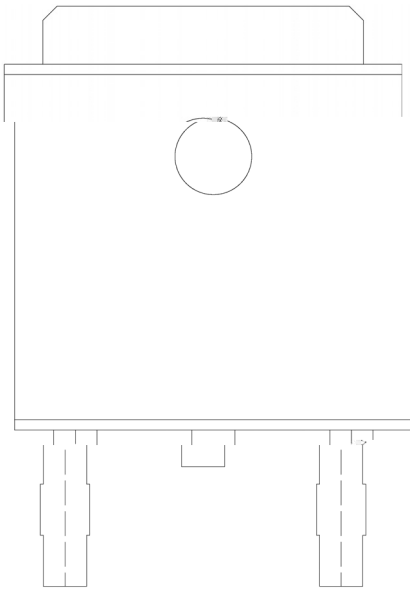
/ Package Dimensions



00	0.90	D	6.45	6.75	12.3	0.4
.00	0.10	D1	5.10	5.50	K	0



/ Marking Instructions



BR

MJD42C

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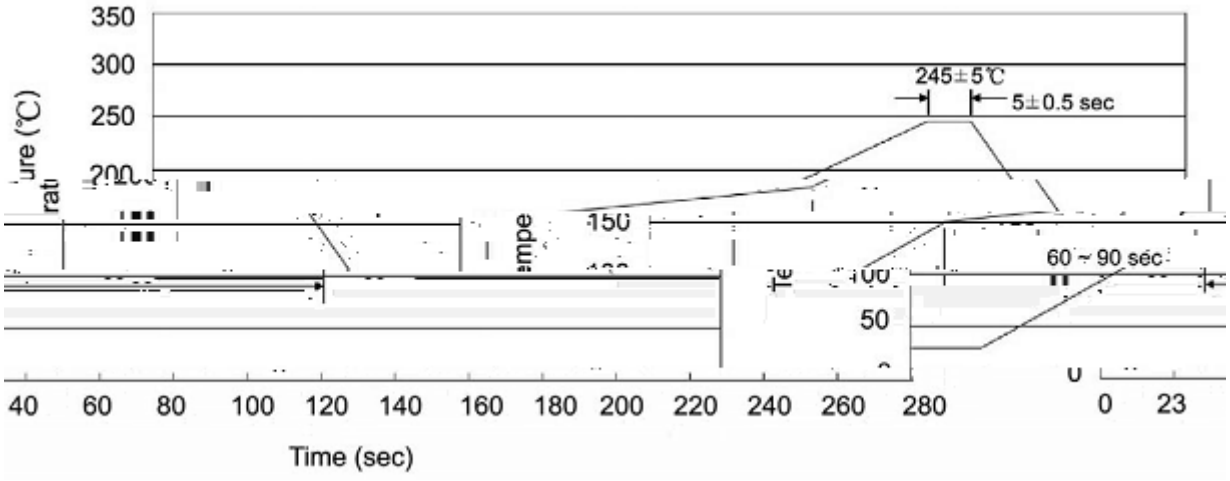
Note:

BR:

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



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